

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-60V	25mΩ@-10V	-40A
	30mΩ@-4.5V	

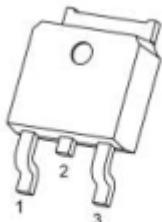
Feature

- High switching speed
- Low Gate Charge
- Excellent package for good heat dissipation

Application

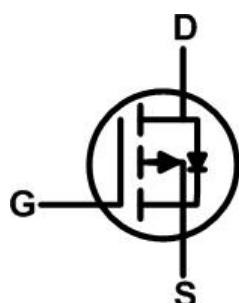
- Load Switches, Adaptor Switch
- Uninterruptible Power Supply

Package

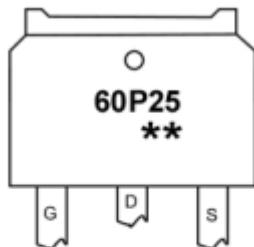


TO-252-2L(G:1 D:2 S:3)

Circuit diagram



Marking



60P25 =Device Code
** =Week Code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

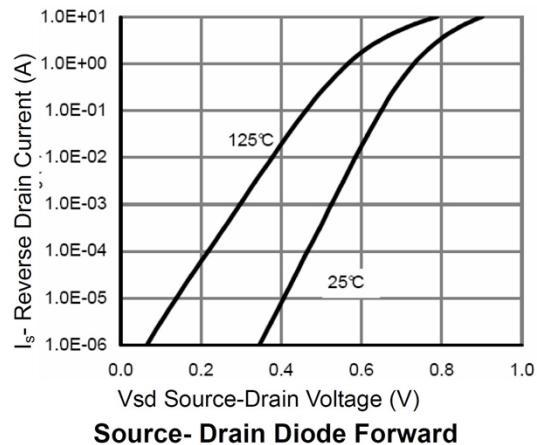
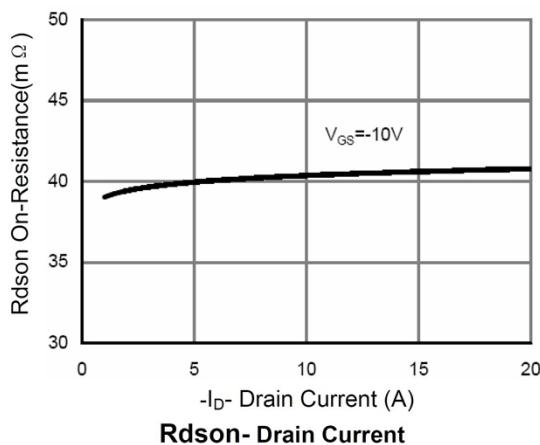
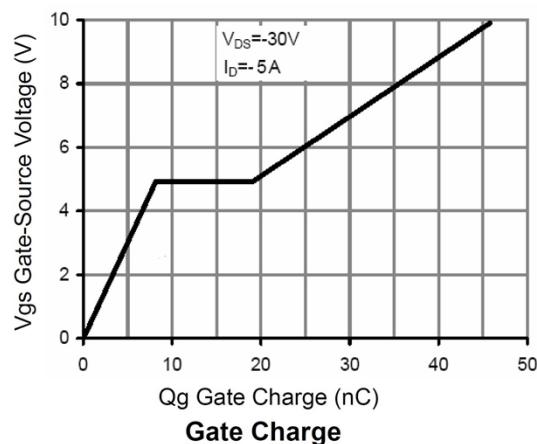
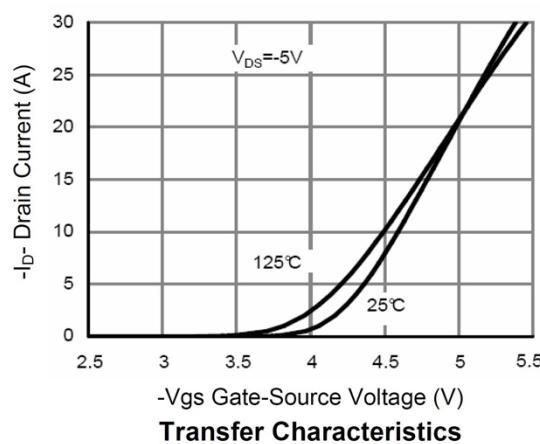
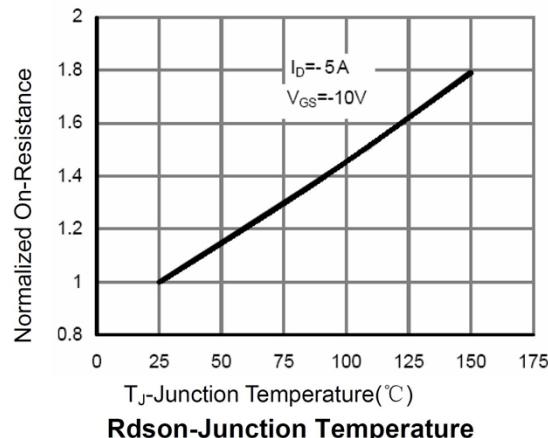
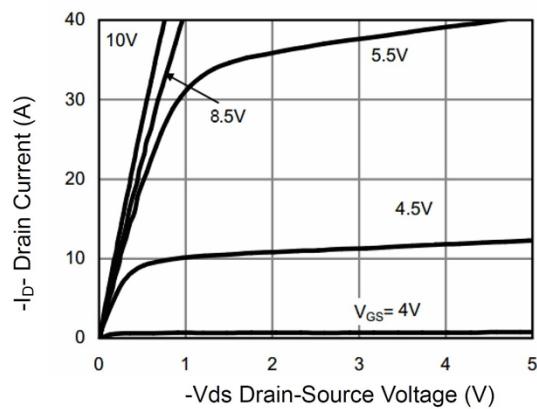
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ($T_c=25^\circ\text{C}$)	I_D	-40	A
Pulse Drain Current Tested	I_{DM}	-160	A
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	P_D	86	W
Thermal Resistance-Junction to Case	$R_{\theta JC}$	1.45	$^\circ\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_{STG}, T_J	-55 to 150	$^\circ\text{C}$

Electrical characteristics

($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{V}, V_{GS} = 0\text{V}$			-1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	μA
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1	-1.7	-2.5	V
Drain-Source On-Resistance	$R_{DS(\text{on})}$	$V_{GS} = -10\text{V}, I_D = -20\text{A}$		25	35	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}, I_D = -15\text{A}$		30	42	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		2588		pF
Output Capacitance	C_{oss}			110		
Reverse Transfer Capacitance	C_{rss}			106		
Switching Characteristics						
Turn-on Delay Time	$T_{d(on)}$	$V_{DD} = -30\text{V}, I_D = -20\text{A}, V_{GEN} = -10\text{V}, R_{GEN} = 3\Omega$		11		nS
Turn-on Rise Time	T_r			5		
Turn-off Delay Time	$T_{d(off)}$			43		
Turn-off Fall Time	T_f			14		
Total Gate Charge	Q_g	$V_{DS} = -30\text{V}, V_{GS} = -10\text{V}, I_D = -20\text{A}$		46		nC
Gate-Source Charge	Q_{gs}			9		
Gate-Drain Charge	Q_{gd}			10		
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$I_{SD} = -1\text{A}, V_{GS} = 0\text{V}$			-1.2	V

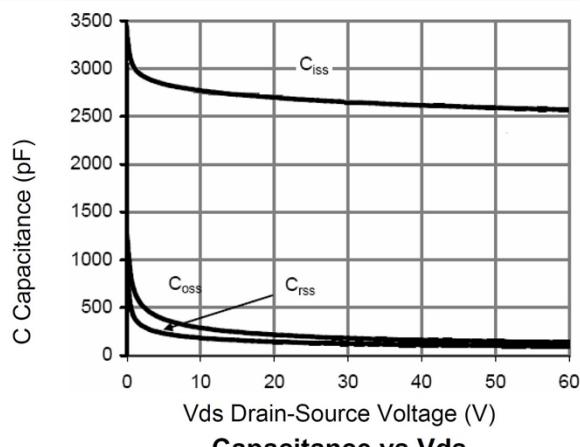
Typical Characteristics



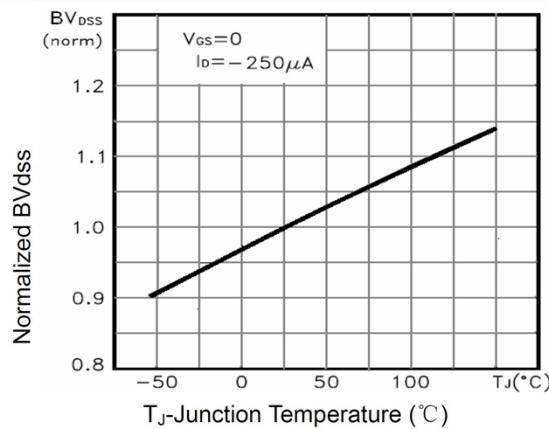
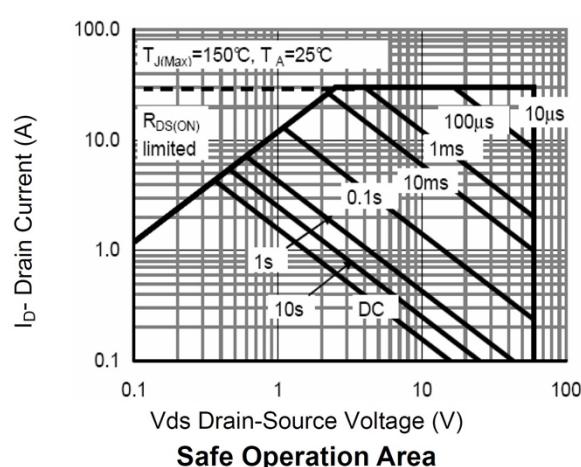


ZL MOSFET

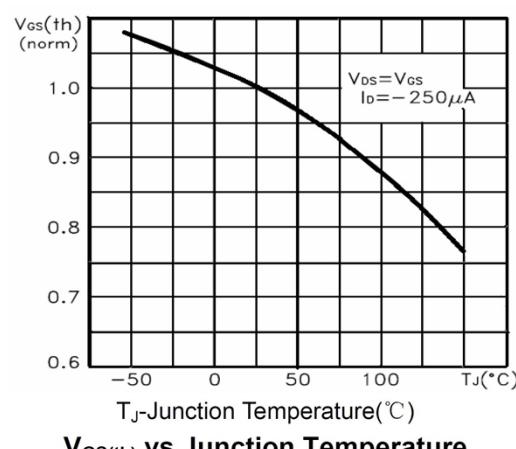
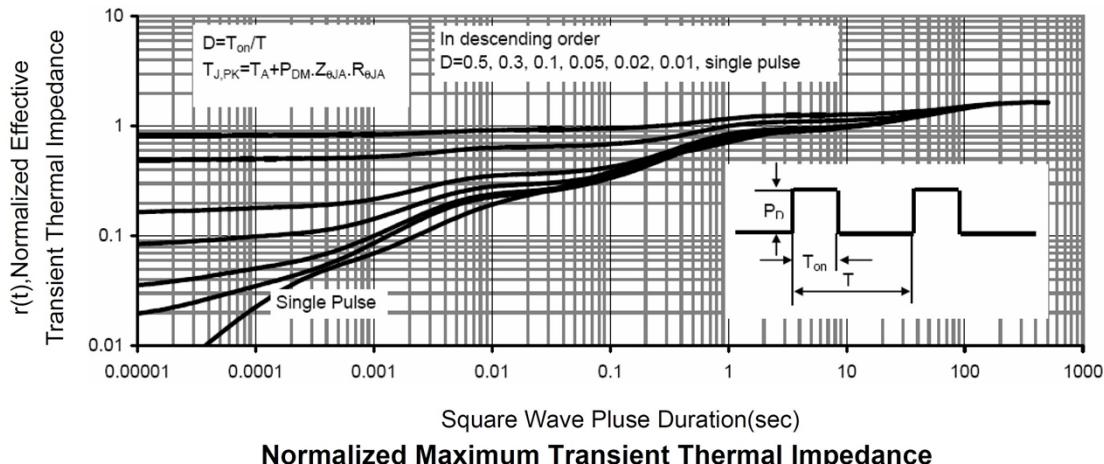
ZL60P25B



Capacitance vs Vds

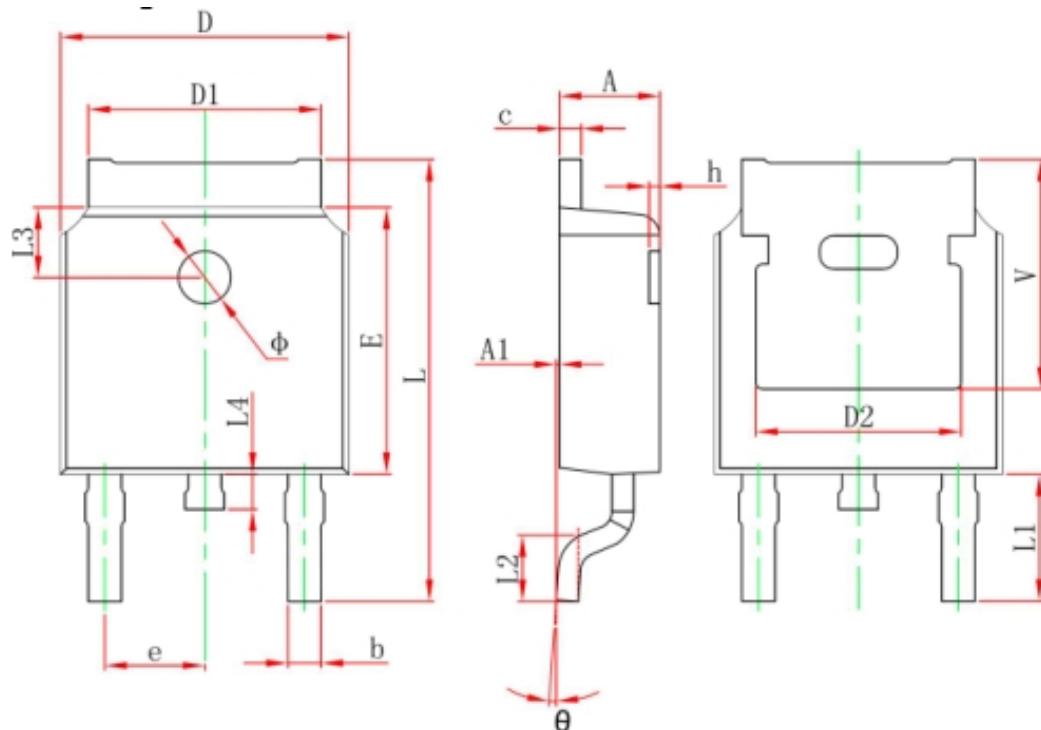
 BV_{DSS} vs Junction Temperature

Safe Operation Area

 $V_{GS(th)}$ vs Junction Temperature

Normalized Maximum Transient Thermal Impedance

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	